N-channel TrenchMOS standard level FET

25 August 2014

Product data sheet

1. General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

2. Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance
- Suitable for standard level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

3. Applications

- 12 V and 24 V loads
- · Automotive and general purpose power switching
- · Motors, lamps and solenoids

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	55	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	-	20.3	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>	-	-	62	W
Static characte	eristics					
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 10 A; T _j = 175 °C; Fig. 11; Fig. 12	-	-	150	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11; Fig. 12	-	64	75	mΩ
Avalanche rug	gedness					
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	I_D = 11 A; $V_{sup} \le 55$ V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped	-	-	30.3	mJ



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	drain		
3	S	source		G_U: 44
mb	D	mounting base; connected to drain	1 3 DODAY (COT404)	mbb076 S
			D2PAK (SOT404)	

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BUK7675-55A	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404			

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK7675-55A	BUK7675-55A

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	55	V
V_{DGR}	drain-gate voltage	R _{GS} = 20 kΩ	-	55	V
V_{GS}	gate-source voltage		-20	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>	-	62	W
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 2; Fig. 3</u>	-	20.3	Α
		T _{mb} = 100 °C; V _{GS} = 10 V; <u>Fig. 2</u>	-	14.3	Α
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \mu s$; Fig. 3	-	81	Α
T _{stg}	storage temperature		-55	175	°C
T _j	junction temperature		-55	175	°C

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Symbol	Parameter	Conditions	Min	Max	Unit
Source-dra	in diode	'	 '		
Is	source current	T _{mb} = 25 °C	-	20.3	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	81	Α
Avalanche	ruggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 11 A; $V_{sup} \le 55$ V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped	-	30.3	mJ

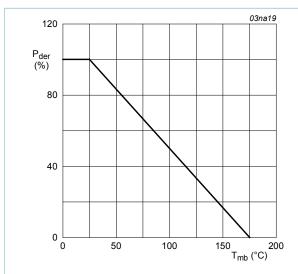


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

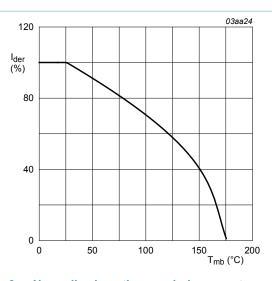


Fig. 2. Normalized continuous drain current as a function of mounting base temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100\%$$

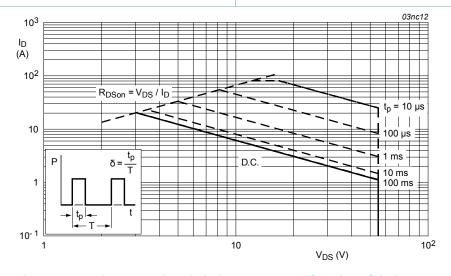


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$$T_{mb} = 25^{\circ}C; I_{DM}$$
 is single pulse

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 4	-	-	2.4	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	mounted on printed-circuit board; minimum footprint	-	50	-	K/W

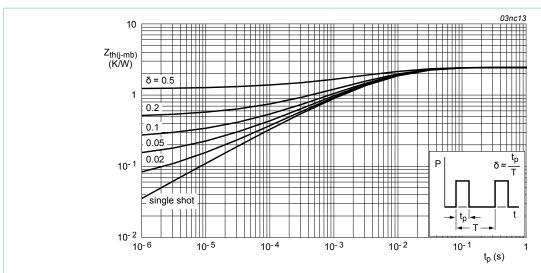


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
Static chara	Static characteristics						
(BIX)D33	drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	55	-	-	V	
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 ^{\circ}\text{C}$	50	-	-	V	
V _{GS(th)} gate-source threshol voltage	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 10	1	-	-	V	
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; Fig. 10	2	3	4	V	
		I_D = 1 mA; V_{DS} = V_{GS} ; T_j = -55 °C; Fig. 10	-	-	4.4	V	
I _{DSS}	drain leakage current	V _{DS} = 55 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μΑ	
		V _{DS} = 55 V; V _{GS} = 0 V; T _j = 25 °C	-	0.05	10	μΑ	

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 10 A; T _j = 175 °C; Fig. 11; Fig. 12	-	-	150	mΩ
		V _{GS} = 10 V; I _D = 10 A; T _j = 25 °C; Fig. 11; Fig. 12	-	64	75	mΩ
Dynamic cl	haracteristics		'	'		
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz;	-	320	483	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 13</u>	-	92	113	pF
C _{rss}	reverse transfer capacitance		-	64	90	pF
t _{d(on)}	turn-on delay time	V_{DS} = 30 V; R_L = 1.2 Ω ; V_{GS} = 10 V; $R_{G(ext)}$ = 10 Ω ; T_j = 25 °C	-	10	-	ns
t _r	rise time		-	50	-	ns
t _{d(off)}	turn-off delay time		-	70	-	ns
t _f	fall time	-	-	40	-	ns
L _D	internal drain inductance	from upper edge of drain mounting base to centre of die; $T_j = 25$ °C	-	2.5	-	nH
		from drain lead 6 mm from package to centre of die; $T_j = 25 ^{\circ}\text{C}$	-	4.5	-	nH
L _S	internal source inductance	from source lead to source bond pad; $T_j = 25 ^{\circ}\text{C}$	-	7.5	-	nH
Source-dra	in diode		l .		1	
V _{SD}	source-drain voltage	I _S = 15 A; V _{GS} = 0 V; T _j = 25 °C; <u>Fig. 14</u>	-	0.85	1.2	V
t _{rr}	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$	-	32	-	ns
Q _r	recovered charge	V_{GS} = -10 V; V_{DS} = 30 V; T_j = 25 °C	-	120	-	nC

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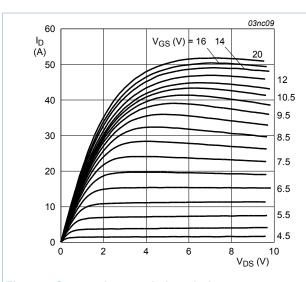


Fig. 5. Output characteristics; drain current as a function of drain-source voltage; typical values



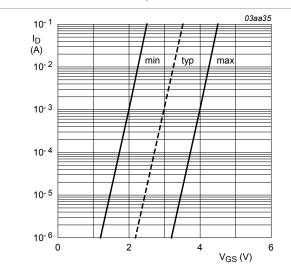


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25\,^{\circ}C; V_{DS} = 5V$$

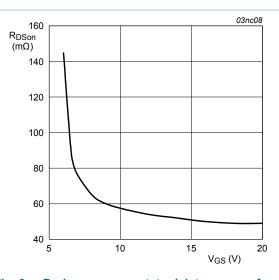


Fig. 6. Drain-source on-state risistance as a function of gate-source voltage; typical values

$$T_j=25^{\circ}C; I_D=10A$$

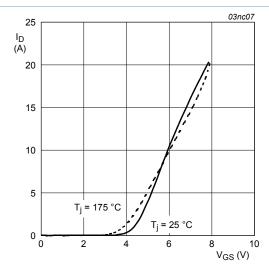


Fig. 8. Transfer characteristics: drain current as a function of gate-source voltage; typical values

$$V_{DS} = 25V$$

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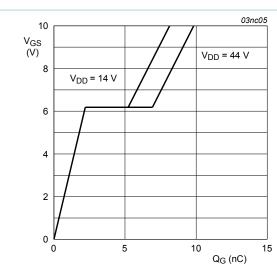


Fig. 9. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25^{\circ}C; I_D = 10A$$

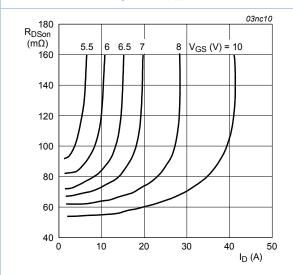


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

$$T_j = 25^{\circ}C$$

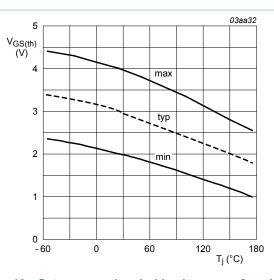


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1 mA; V_{DS} = V_{GS}$$

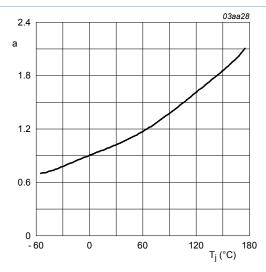


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

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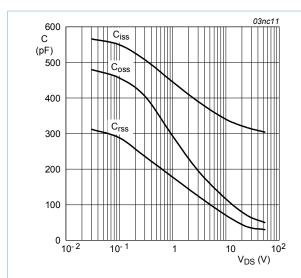


Fig. 13. Input, output and reverse capicitances as a function of drain-source voltage; typical values

$$V_{GS} = 0V; f = 1MHz$$

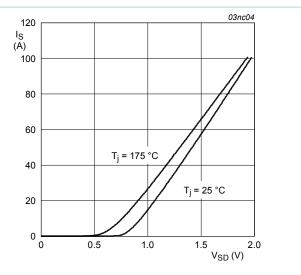
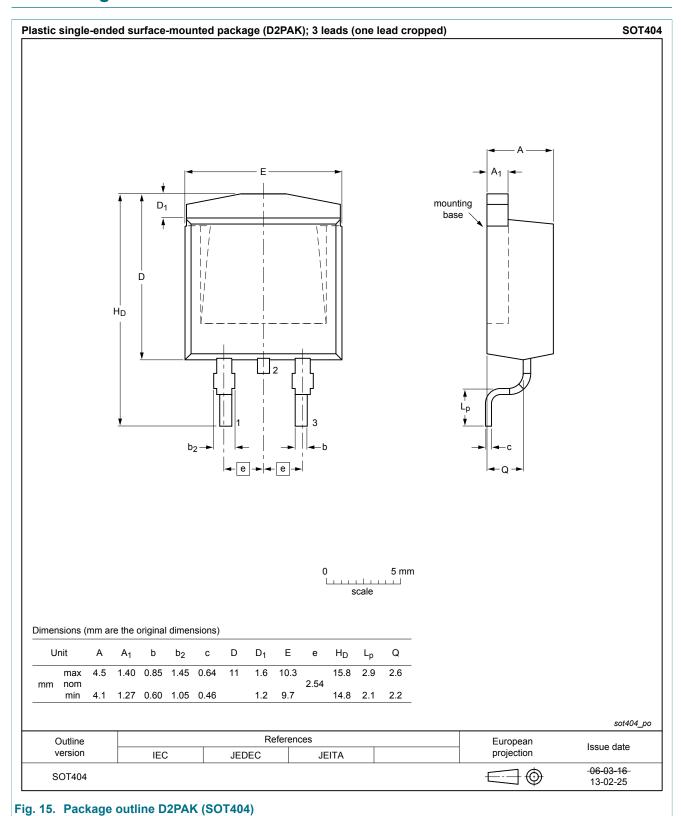


Fig. 14. Reverse diode current as a function of reverse dioode voltage; typical values

$$V_{GS} = 0V$$

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11. Package outline



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